

## Process Change Notice

**Parts Affected:**

Chip process CPD64, Low Leakage Diode discrete semiconductors, wafers, and die in chip form.

**Extent of Change:**

The overall wafer diameter is being increased from 4 inch to 5 inch.  
The overall die thickness is being reduced from 8 mils to 5.9 mils

**Reason for Change:**

Process transfer from the 4" wafer fab to the 5" wafer fab.

**Effect of Change:**

This change does not affect the electrical characteristics of any device.

**Effective Date of Change:**

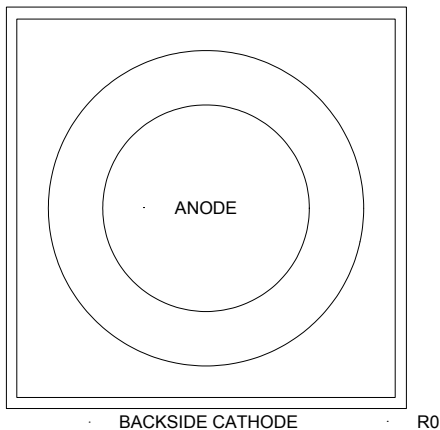
Existing inventory will be shipped until depleted.

**Sample Availability:**

Please contact Salesperson or Manufacturer's Representative.

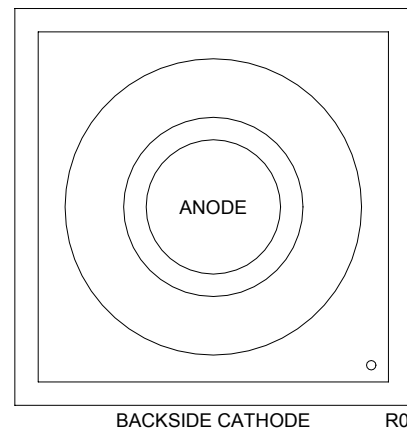
**Figures:**

**Figure 1: CPD64 Chip Geometry**



Die Size:	17.5 x 17.5 mils
Die Thickness:	8.0 mils
Bond Pad Area (Anode):	8.0 mils diameter
Topside Metal:	Al (30,000Å)
Backside Metal:	Au (6,000Å)
Gross Die per 4" wafer:	34,368

**Figure 2: CPD66X Chip Geometry**



Die Size:	17.5 x 17.5 mils
Die Thickness:	5.9 mils
Bond Pad Area (Anode):	8.0 mils diameter
Topside Metal:	Al (30,000Å)
Backside Metal:	Au-As (13,000Å)
Gross Die per 5" wafer:	54,848



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**PCN # 110**

**Notification Date:**

**21 April 2009**

**Part Numbers Affected:**

CPD64-CLL459A-CT  
CPD64-CMPD3003-CT  
CPD64-CMPD3003-WN  
CPD64-1N3595-CT  
CPD64-1N3595-WN  
CPD64-1N3595-WR  
CPD64-1N457A-CT  
CPD64-1N485B-CT

CMDD3003  
CMLD3003DOG  
CMOD3003  
CMPD3003  
CMPD3003A  
CMPD3003C  
CMPD3003S  
CMHD457A  
CMHD459A  
CMHD3595